

## 1350V, 15A, Trench FS Gen.7 IGBT

### General Description

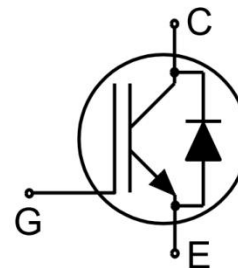
Using NCE's proprietary high density trench gate design and advanced FS (Field Stop) Gen.7 technology, the 1350V Trench Field Stop Gen.7 IGBT offers superior conduction and switching performances, and easy parallel operation;

### Features

- Trench Field Stop Gen.7 Technology Offering
- Low saturation voltage:  $V_{CEsat} = 1.80V(Typ.) @ I_C = 15 A$
- High speed switching, Low switching losses
- Maximum junction temperature  $T_{vjmax} = 175^{\circ}C$
- Tighten parameter distribution
- High ruggedness, temperature stable behavior
- Pb-free lead plating; RoHS compliant

### Application

- Inductive Cooking
- Soft Switching Applications



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE15ER135LP	TO-3P-3L	NCE15ER135LP



TO-3P-3L

### Absolute Maximum Ratings ( $T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	30	A
	Collector Current @ $T_C = 100^{\circ}C$	15	A
$I_{Cpuls}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	45	A
-	Turn off safe operating area, $V_{CE}=1350V$ , $T_j=175^{\circ}C$	45	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^{\circ}C$	15	A
$I_{FM}$	Diode Maximum Forward Current	45	A
$P_D$	Power Dissipation @ $T_C = 25^{\circ}C$	155	W
	Power Dissipation @ $T_C = 100^{\circ}C$	77	W
$T_{stg}$	Storage Temperature	-55 to +150	$^{\circ}C$
$T_{vj}$	Operating junction temperature	-40 to +175	$^{\circ}C$
$T_L$	Maximum Temperature for Soldering	260	$^{\circ}C$

## Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.96	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	1.62	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}\text{C}/\text{W}$

## Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Value			Units
			Min.	Typ.	Max.	
Static Characteristics						
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	V <sub>GE</sub> =0V, I <sub>CE</sub> =1mA	1350	--	--	V
I <sub>CES</sub>	Collector-Emitter Leakage Current	V <sub>GE</sub> =0V, V <sub>CE</sub> =1350V	--	--	15	uA
I <sub>GES(F)</sub>	Gate to Emitter Forward Leakage	V <sub>GE</sub> =+30V, V <sub>CE</sub> =0V	--	--	100	nA
I <sub>GES(R)</sub>	Gate to Emitter Reverse Leakage	V <sub>GE</sub> =-30V, V <sub>CE</sub> =0V	--	--	100	nA
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =7.5A    V <sub>GE</sub> =15V,	--	1.50	--	V
		I <sub>C</sub> =15A        T <sub>J</sub> =25°C	--	1.80	2.20	V
		I <sub>C</sub> =7.5A    V <sub>GE</sub> =15V,	--	1.70	--	V
		I <sub>C</sub> =15A        T <sub>J</sub> =175°C	--	2.20	--	V
V <sub>GE(th)</sub>	Gate Threshold Voltage	I <sub>C</sub> =1mA, V <sub>CE</sub> =V <sub>GE</sub>	5.00	5.75	6.50	V
Dynamic Characteristics						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz	1300	1630	1900	pF
C <sub>oes</sub>	Output Capacitance		--	30	--	
C <sub>res</sub>	Reverse Transfer Capacitance		--	10	--	
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> =960V, I <sub>C</sub> =15A, V <sub>GE</sub> =15V	--	58	--	nC
Q <sub>ge</sub>	Gate to Emitter Charge		--	27	--	
Q <sub>gc</sub>	Gate to Collector Charge		--	16	--	
R <sub>g</sub>	Internal Gate Resistance	F=1MHz	--	2.8	--	Ω
Switching Characteristics						
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>CE</sub> =600V, I <sub>C</sub> =15A, V <sub>GE</sub> =0/15V, R <sub>g</sub> =15Ω  Inductive Load	--	22	--	ns
t <sub>r</sub>	Rise Time		--	18	--	
t <sub>d(OFF)</sub>	Turn-Off Delay Time		--	166	--	
t <sub>f</sub>	Fall Time		--	71	--	
E <sub>on</sub>	Turn-On Switching Loss		--	0.63	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	0.44	--	
E <sub>ts</sub>	Total Switching Loss		--	1.07	--	

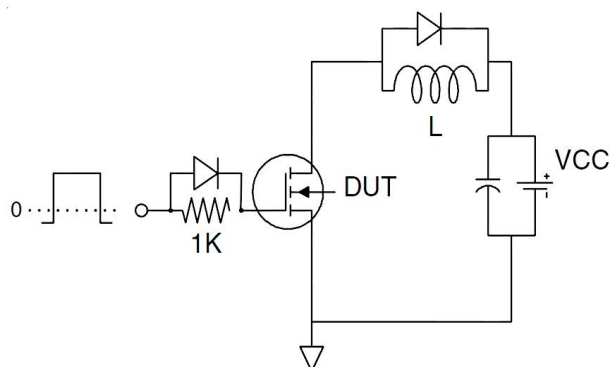
## Electrical Characteristics of the Diode ( $T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions		Rating			Units
				Min.	Typ.	Max.	
$V_{FM}$	Diode Forward Voltage	$I_F = 15\text{A}$	$T_J = 25^\circ\text{C}$	--	2.5	3.0	V
$T_{rr}$	Reverse Recovery Time	$V_R = 600\text{V}, I_F = 15\text{A},$ $R_g = 15\Omega, T_J = 25^\circ\text{C}$		--	135	--	ns
$I_{RRM}$	Diode Peak Reverse Recovery Current			--	22	--	A
$Q_{rr}$	Reverse Recovery Charge			--	1.48	--	$\mu\text{C}$
$E_{rec}$	Reverse recovery energy			--	0.06	--	mJ

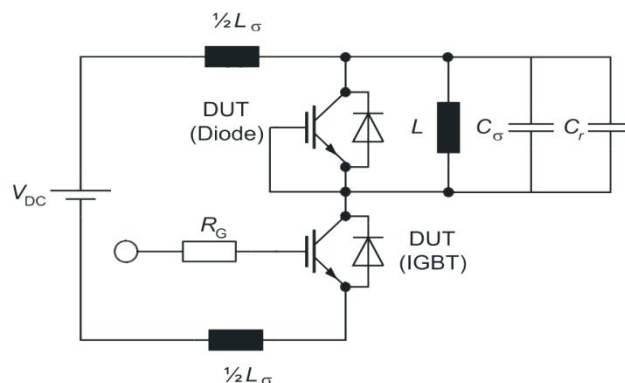
Note: For optimum lifetime and reliability, NCE recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

## Test Circuit

### 1) Gate Charge Test Circuit

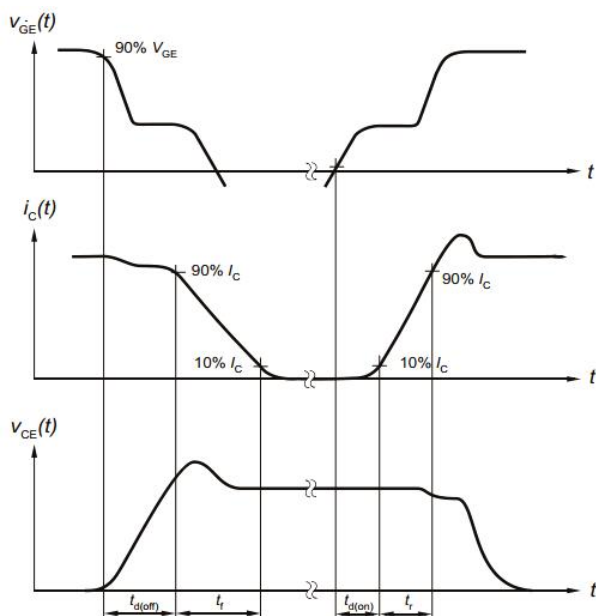


### 2) Switch Time Test Circuit

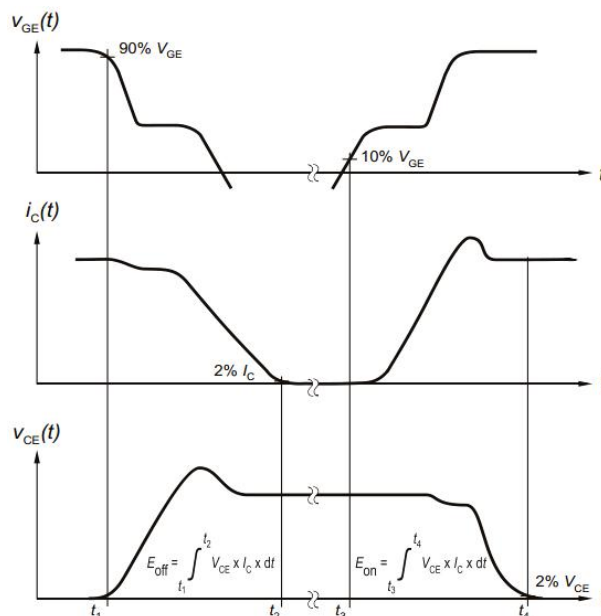


## Switching characteristics

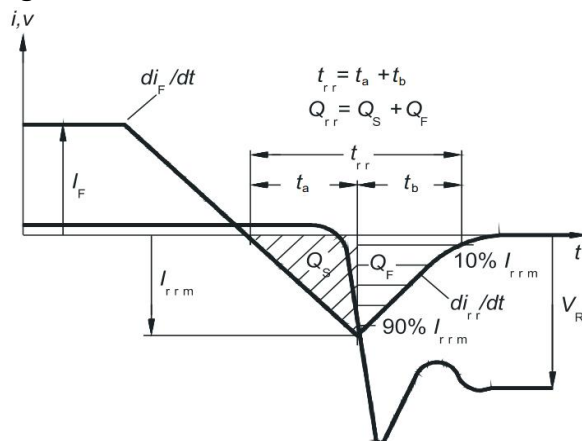
### 1) Definition of switching times



### 2) Definition of switching losses

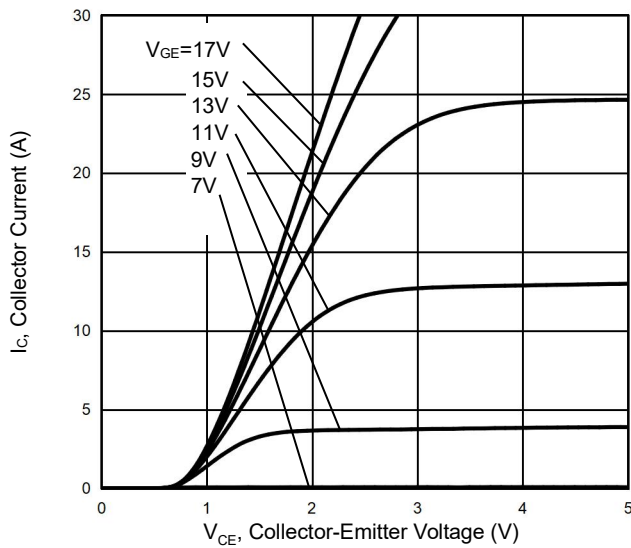


### 3) Definition of diode switching characteristics

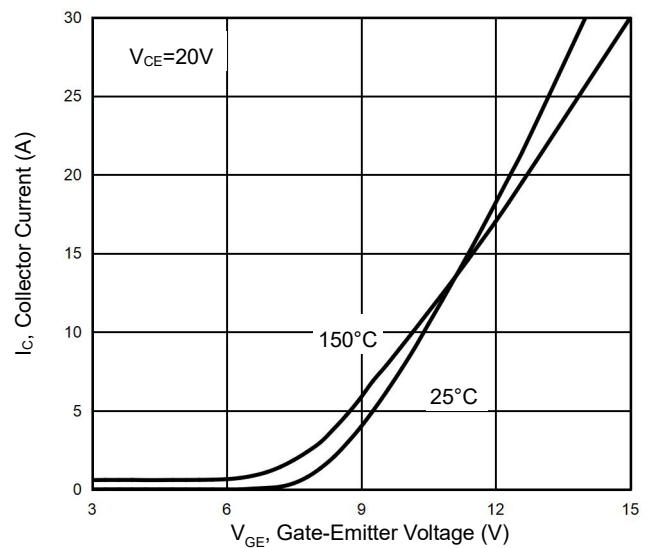


## Typical Electrical and Thermal Characteristics

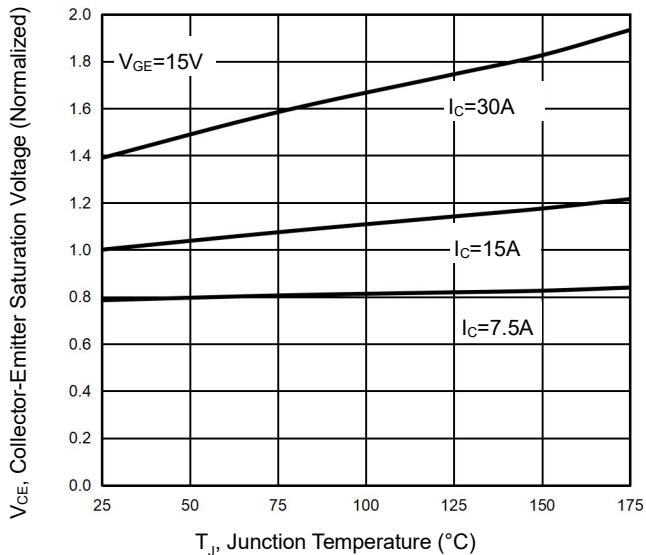
**Figure 1 Output Characteristics**



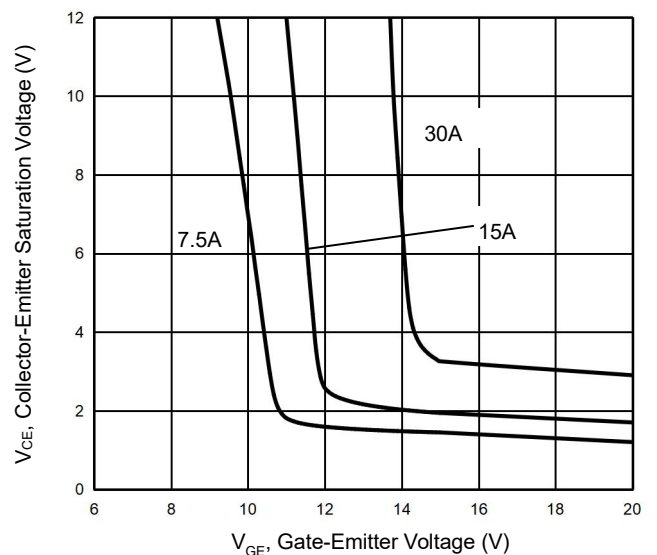
**Figure 2 Transfer Characteristics**



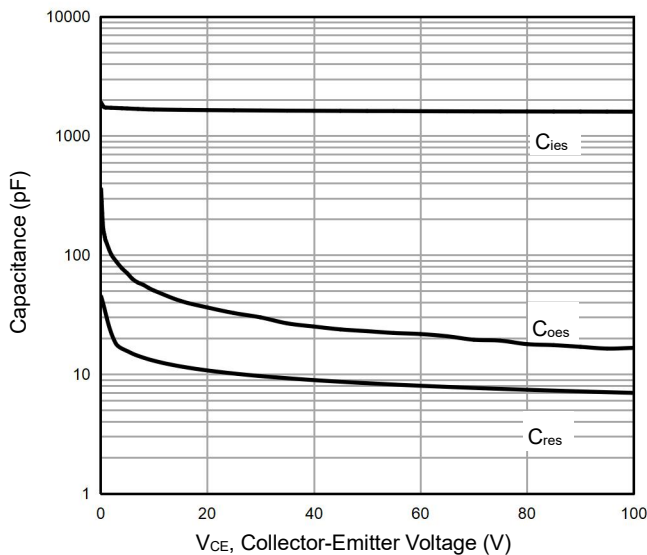
**Figure 3  $V_{CE(sat)}$  vs. Case Temperature**



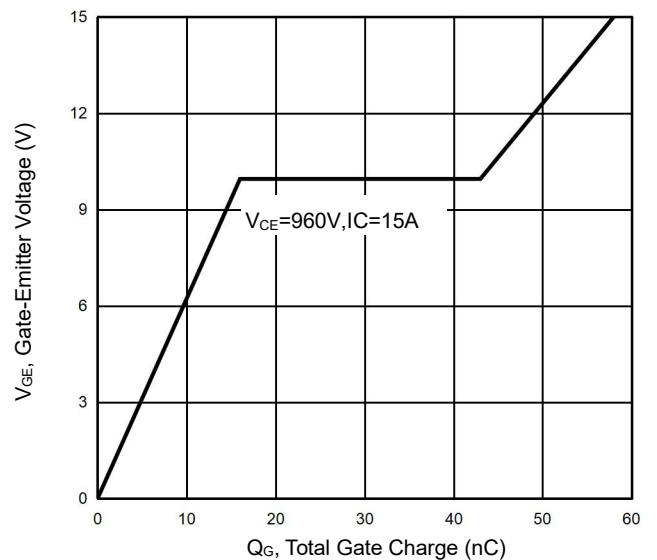
**Figure 4 Saturation Voltage vs.  $V_{GE}$**



**Figure 5 Capacitance Characteristics**

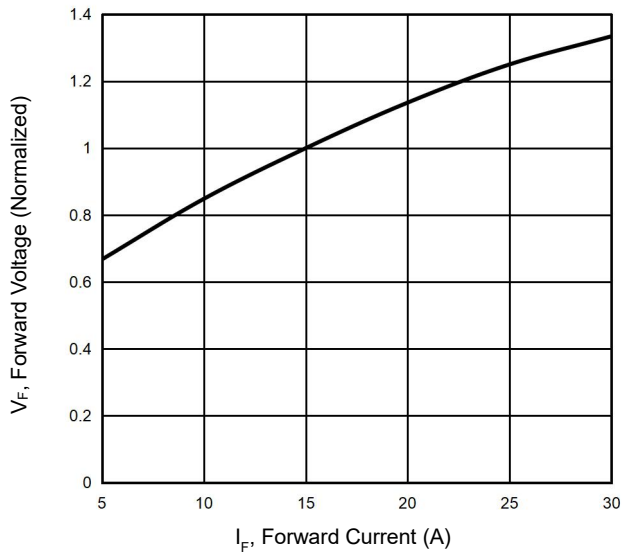


**Figure 6 Gate Charge Wave Form**

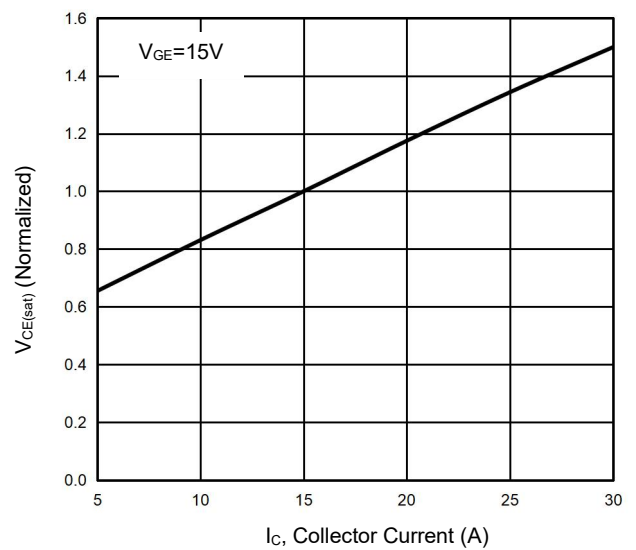


## Typical Electrical and Thermal Characteristics

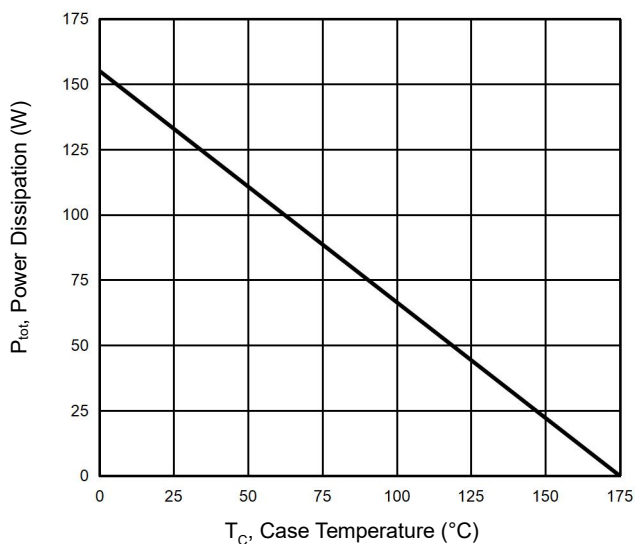
**Figure 7 Forward Characteristics**



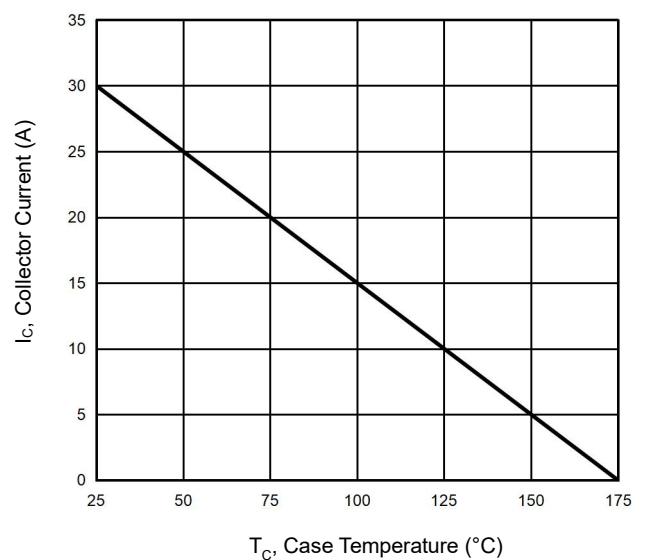
**Figure 8 Typical Collector-Emitter Saturation Voltage as a function of Collector Current**



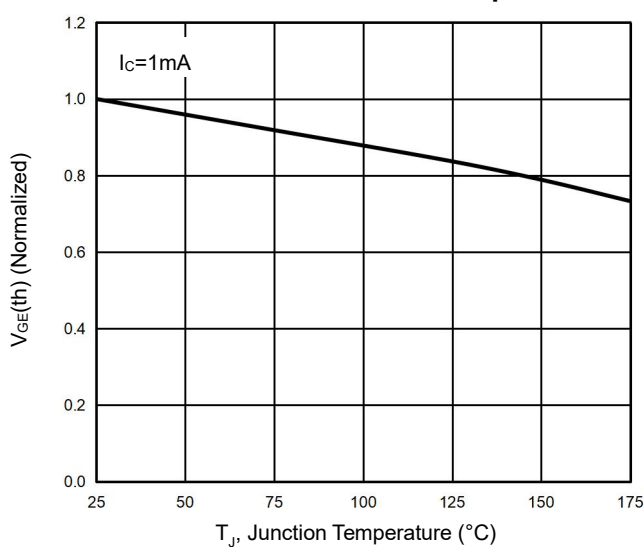
**Figure 9  $P_{tot}$  vs. Case Temperature**



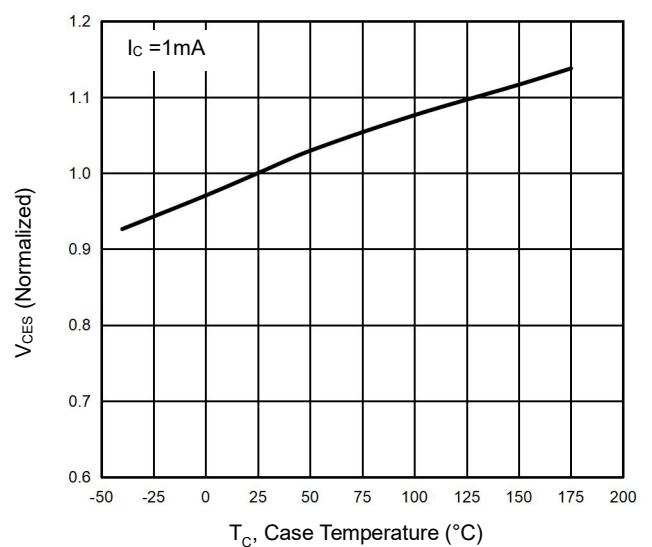
**Figure 10  $I_C$  vs. Temperature**



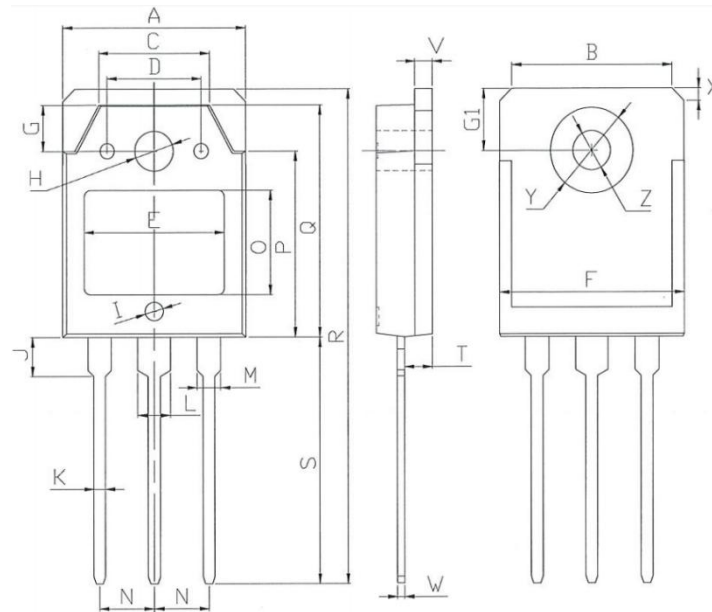
**Figure 11 Gate-Emitter Threshold Voltage as a Function of Junction Temperature**



**Figure 12  $V_{CES}$  vs. Case Temperature**



## TO-3P-3L-L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.40	15.80	0.61	0.62
B	13.40	13.80	0.53	0.54
C	9.30	9.70	0.37	0.38
D	7.80	8.20	0.31	0.32
E	11.65	12.05	0.46	0.47
F	15.45	15.85	0.61	0.62
G	3.60	4.00	0.14	0.16
G1	4.80	5.20	0.19	0.20
H	3.30	3.70	0.13	0.15
I	1.30	1.70	0.05	0.07
J	3.00	3.40	0.12	0.13
K	0.90	1.10	0.04	0.05
L	3.00	3.20	0.12	0.13
M	2.00	2.20	0.08	0.09
N	5.25	5.65	0.21	0.22
O	8.20	8.60	0.32	0.34
P	13.70	14.10	0.54	0.56
Q	18.50	18.90	0.73	0.74
R	39.50	40.50	1.56	1.59
S	19.70	20.30	0.78	0.80
T	2.20	2.60	0.09	0.10
V	1.40	1.60	0.06	0.07
W	0.50	0.70	0.02	0.03
X	1.50	2.10	0.06	0.08
Y	6.80	7.20	0.27	0.28
Z	3.00	3.40	0.12	0.13

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